NSN 5961-01-314-1986

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-314-1986 **Inclosure Material:** Metal **Overall Length:** 0.185 inches **Terminal Length:** 0.500 inches **Overall Diameter:** 0.370 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-99 **Component Name And Quantity:** 2 transistor **Mounting Method: Terminal Terminal Circle Diameter:** 0.200 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 30.0 collector to base voltage/static/emitter open all transistor and 15.0 collector to emitter voltage/static/base open all transistor and 3.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 50.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 600.0 milliwatts small-signal input power, common-collector absolute all transistor **Transfer Ratio:** 0.9 static forward current transfer ratio, common-emitter all transistor and 1.0 static forward current transfer ratio, common-emitter all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 6 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: